

ABSTRACT OF THE DISCLOSURE

There is provided a transistor and a method of manufacturing this transistor that allow a high degree of freedom when designing a wiring structure and also allow an improvement in product quality to be achieved. The transistor includes a source area, a drain area, and a channel area, each of which are formed by semiconductor films, and also a gate insulating film and a gate electrode. The semiconductor film containing the source area and the semiconductor film containing the drain area are formed separately sandwiching both sides of an insulating member. The semiconductor film containing the channel area is formed on top of the insulating member.